

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
100V	130mΩ@10V	3A
	140mΩ@4.5V	

Feature

- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

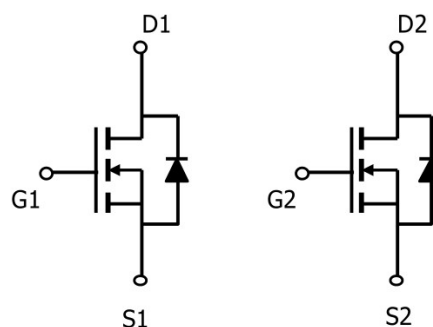
- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply

Package

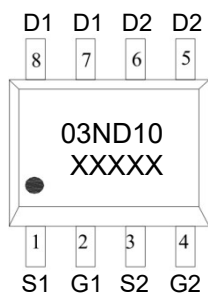


SOP-8

Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	3	A
Pulsed Drain Current	I_{DM}	12	A
Power Dissipation	P_D	2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	85	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}C$

Electrical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	2	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 3A$		95	130	m Ω
		$V_{GS} = 4.5V, I_D = 1A$		100	140	
Dynamic characteristics ¹⁾						
Input Capacitance	C_{iss}	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$		730		pF
Output Capacitance	C_{oss}			37		
Reverse Transfer Capacitance	C_{rss}			27		
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V, I_D = 3A$		21.5		nC
Gate-Source Charge	Q_{gs}			3.2		
Gate-Drain Charge	Q_{gd}			6		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50V, R_L = 15\Omega$ $V_{GS} = 10V, R_G = 2.5\Omega$		11		nS
Turn-on rise time	t_r			7.4		
Turn-off delay time	$t_{d(off)}$			35		
Turn-off fall time	t_f			9.1		
Source-Drain Diode characteristics						
Diode Forward voltage	V_{DS}	$V_{GS} = 0V, I_S = 3A$			1.2	V

Notes:

1) Guaranteed by design, not subject to production testing.

Typical Characteristics

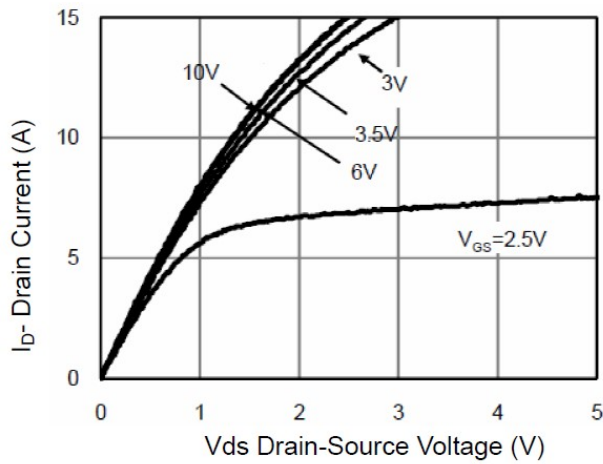


Figure 1 Output Characteristics

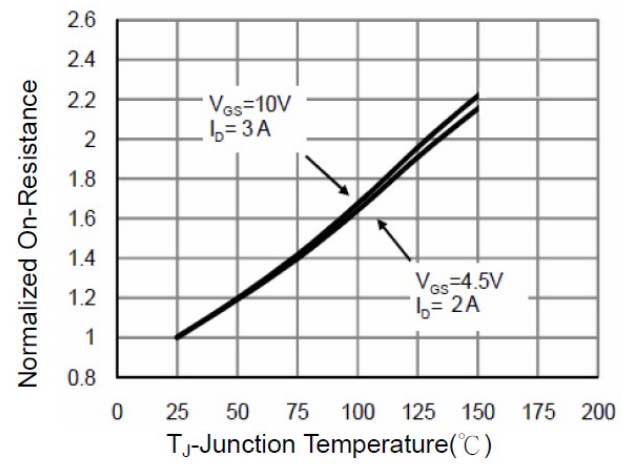


Figure 2 $R_{DS(on)}$ -Junction Temperature

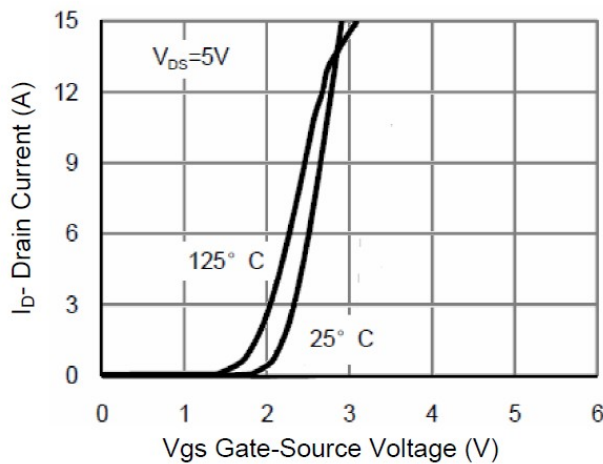


Figure 3 Transfer Characteristics

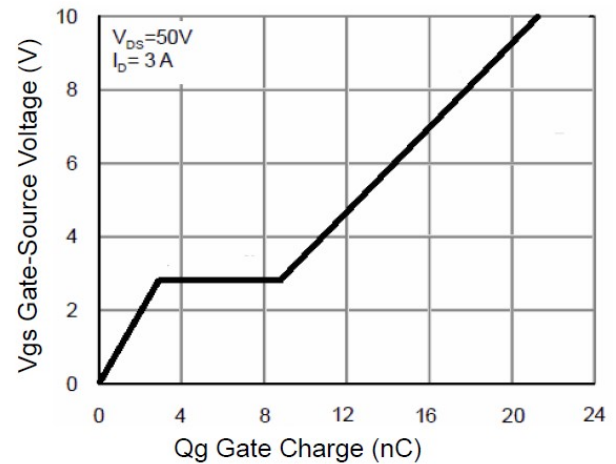


Figure 4 Gate Charge

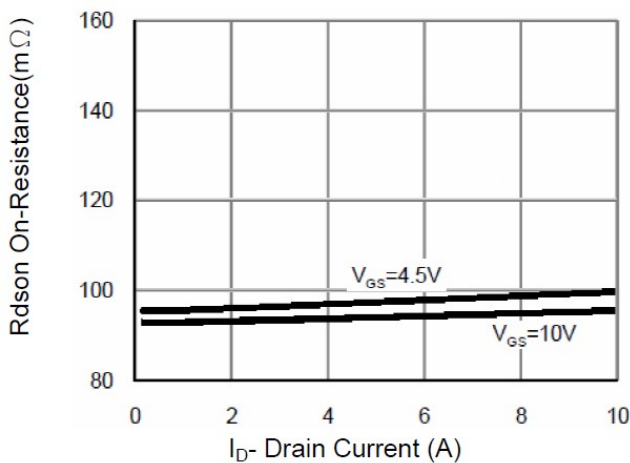


Figure 5 $R_{DS(on)}$ - Drain Current

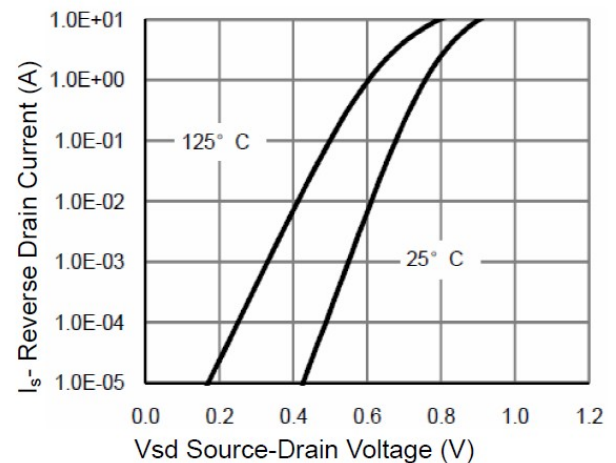


Figure 6 Source- Drain Diode Forward

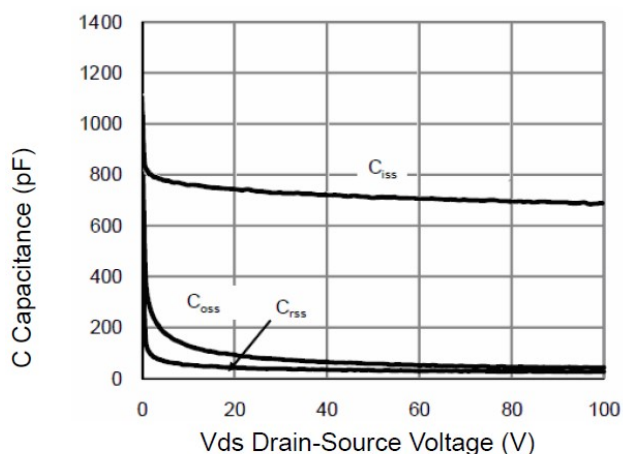


Figure 7 Capacitance vs Vds

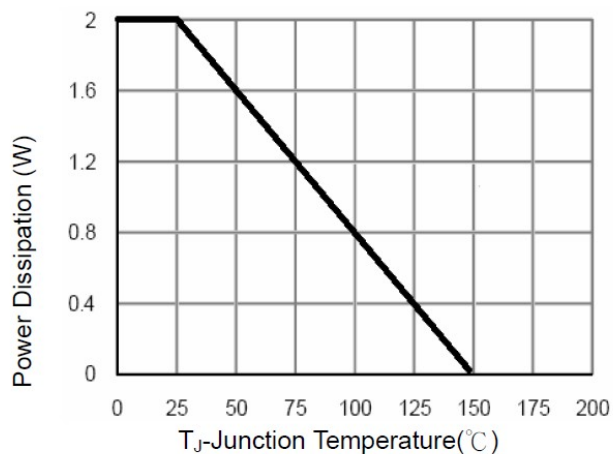


Figure 8 Power De-rating

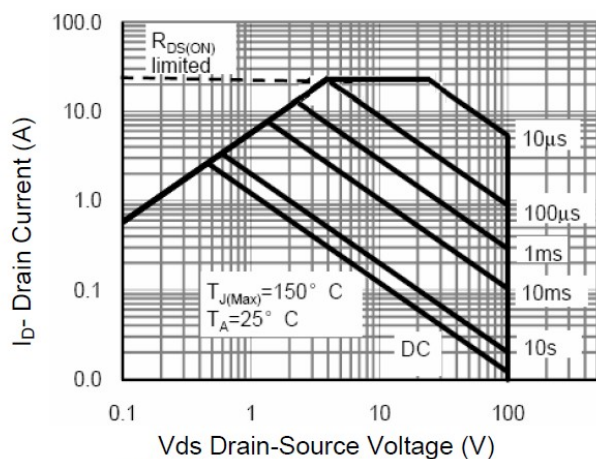


Figure 9 Safe Operation Area

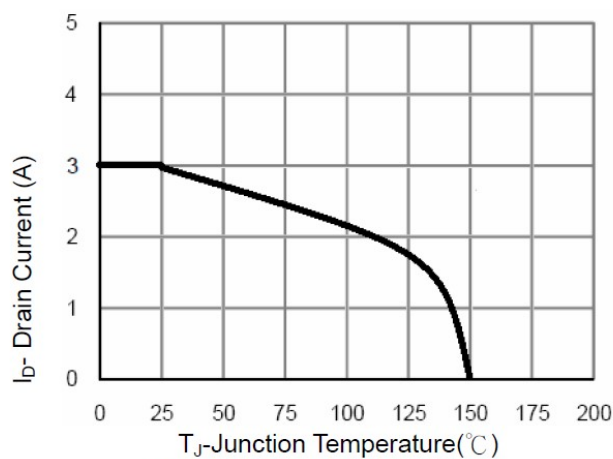


Figure 10 Current De-rating

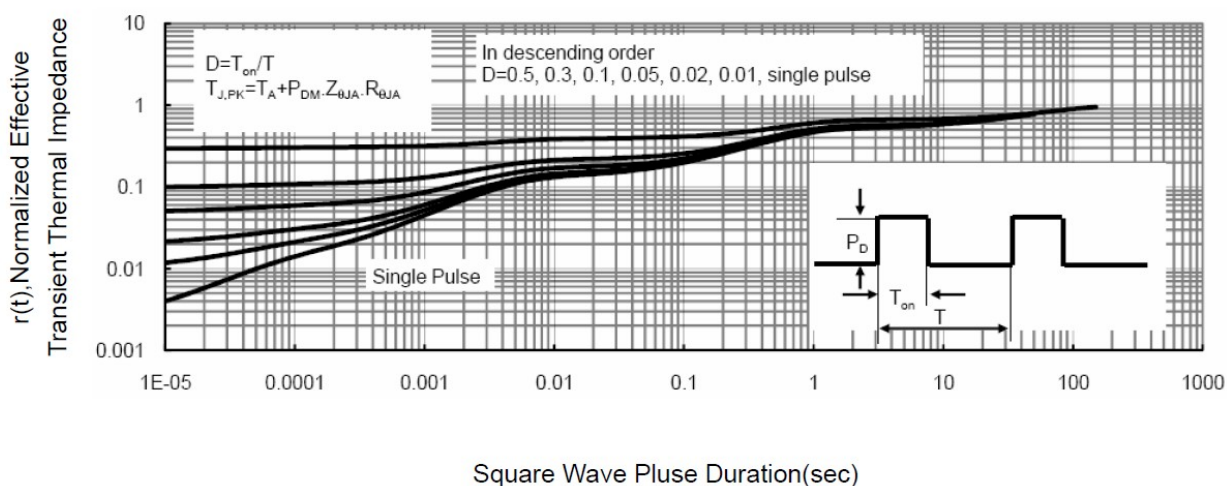
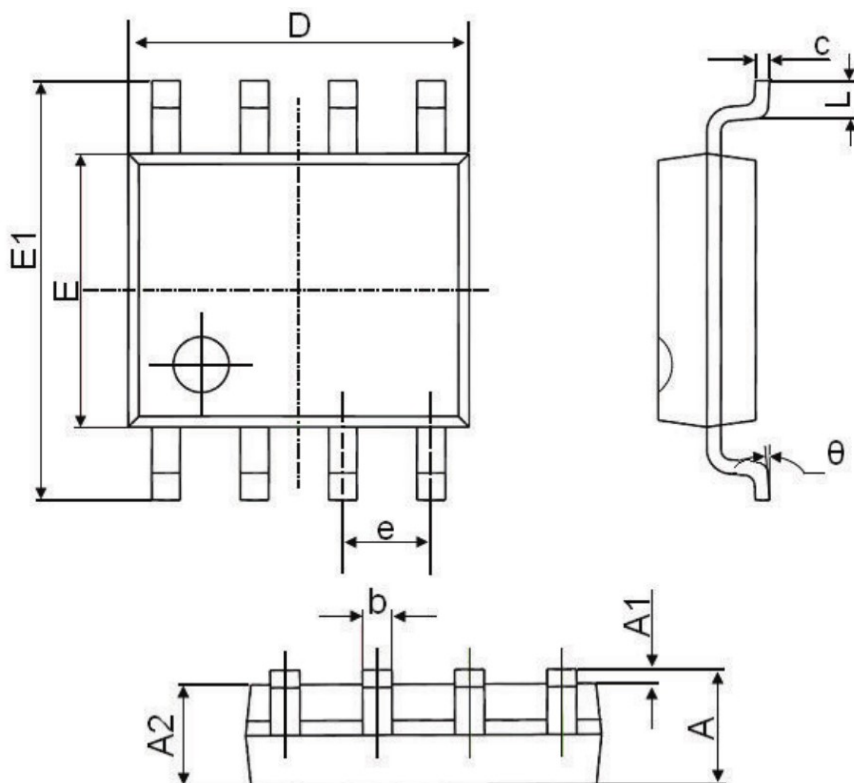


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.250	1.650	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°